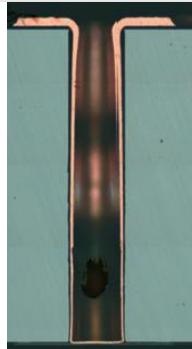


In our **wafer face-up** electroplating system, the reaction chamber and wafer position is inverted, thus preventing air trapping during plating. The electrolyte flow is determined by the flow gap of the chamber and the pressure from the liquid column. The system can be used bench top system in standard fume hoods for research and development.

Application

- Through silicon via (Cu TSV)
- Plating at high aspect ratio
- Dual-damascene process



Features & Advantages

- Wafer face-up setup avoids air trapping
- Gravity assisted plating
- Substrate size: 100 mm, 150 mm, 200 mm
- Bath volume: 20 liters

